

isc Silicon NPN Power Transistor

3DD207i

**DESCRIPTION**

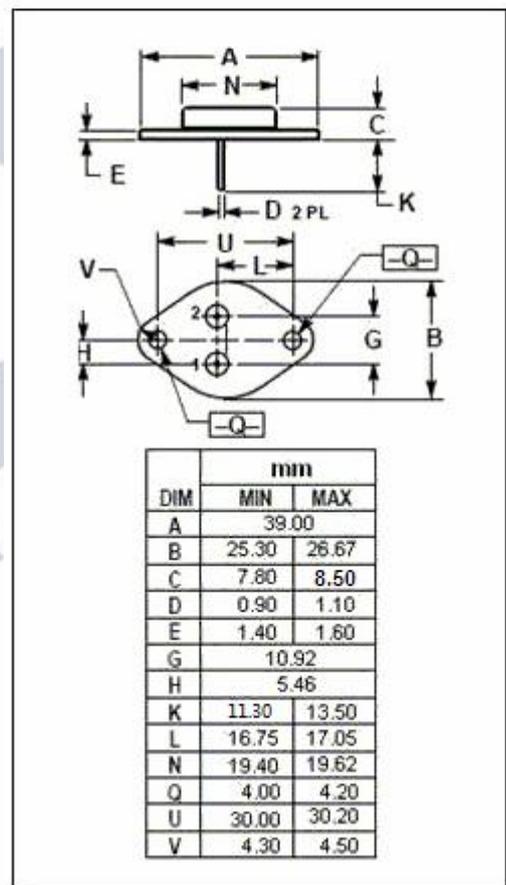
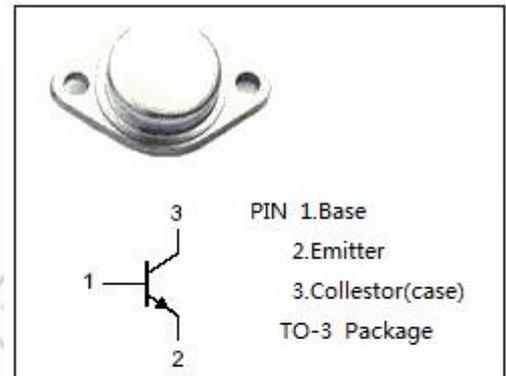
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 200V(\text{Min.})$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C = 3A$

**APPLICATIONS**

- Designed for auto amplifier application.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	200	V
$V_{CEO}$	Collector-Emitter Voltage	200	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	5	A
$P_C$	Collector Power Dissipation@ $T_C=75^\circ\text{C}$	50	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



**isc Silicon NPN Power Transistors****3DD207i****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=50\text{mA}; I_B=0$	200		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=1\text{mA}; I_E=0$	200		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=1\text{mA}; I_C=0$	6		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.3\text{A}$		1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=200\text{V}; I_E=0$		0.5	mA
$h_{FE}$	DC Current Gain	$I_C=1\text{A}; V_{CE}=4\text{V}$	100	200	